

L Number	Hits	Search Text	DB	Time stamp
1	3360	174/261	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 22:55
2	1265	174/256	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 23:05
3	1062	174/257	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 23:05
-	4898	257/758	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 19:51
-	7307	wafer same (peripheral or edge) with (recess or open\$3 or via or aperture or hole or cavity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:48
-	4572	wafer with (peripheral or edge) with (recess or open\$3 or via or aperture or hole or cavity)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:49
-	571	wafer with (peripheral or edge) with (recess or open\$3 or via or aperture or hole or cavity) and (dielectric or insulat\$3) with (peripheral or edge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:52
-	95	(wafer with (peripheral or edge) with (recess or open\$3 or via or aperture or hole or cavity) and (dielectric or insulat\$3) with (peripheral or edge)) and wafer with multi\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 18:52
-	972	257/759	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 20:08
-	1259	257/760	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 20:12
-	479	257/761	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 20:33
-	1486	257/762	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 20:37
-	2626	257/751	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 21:17
-	3219	dielectric near constant with (silicon near nitride or "Si" near "N")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/25 20:46

-	1233	257/754	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/25 21:26
-	847	257/755	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/25 21:29
-	424	257/756	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/25 21:36
-	737	257/757	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/25 21:37